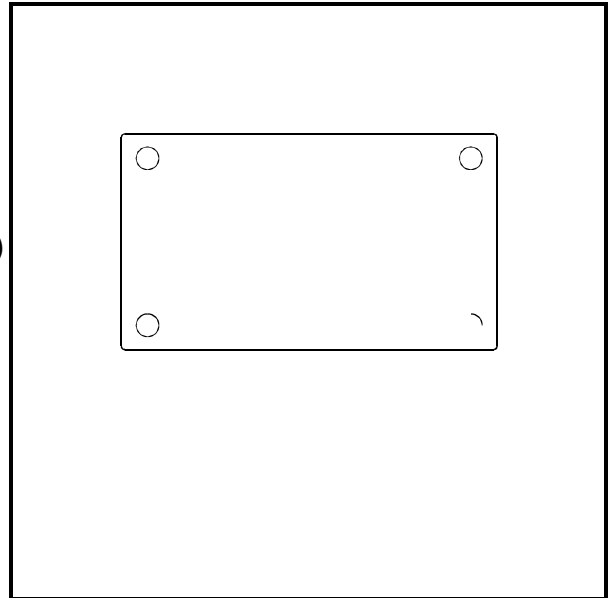


IGBT MODULE (N series)**■ Features**

- *Square RBSOA*
- *Low Saturation Voltage*
- *Less Total Power Dissipation*
- *Improved FWD Characteristic*
- *Minimized Internal Stray Inductance*
- *Overcurrent Limiting Function (~3 Times Rated Current)*

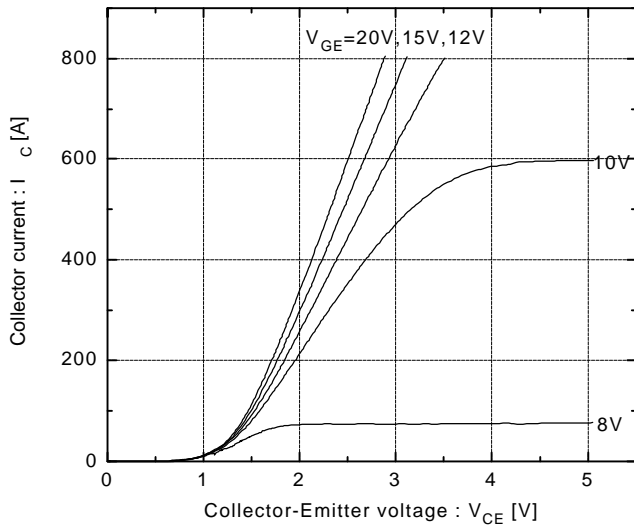
■ Applications

- *High Power Switching*
- *A.C. Motor Controls*
- *D.C. Motor Controls*
- *Uninterruptible Power Supply*

■ Outline Drawing

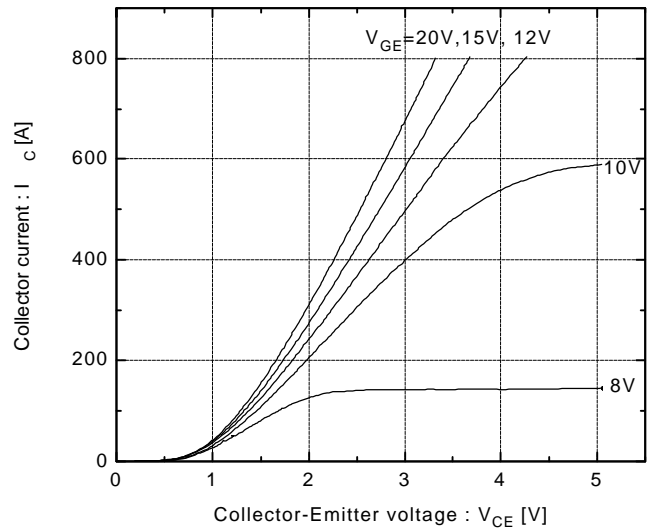
Collector current vs. Collector-Emmitter voltage

$T_j=25^\circ\text{C}$



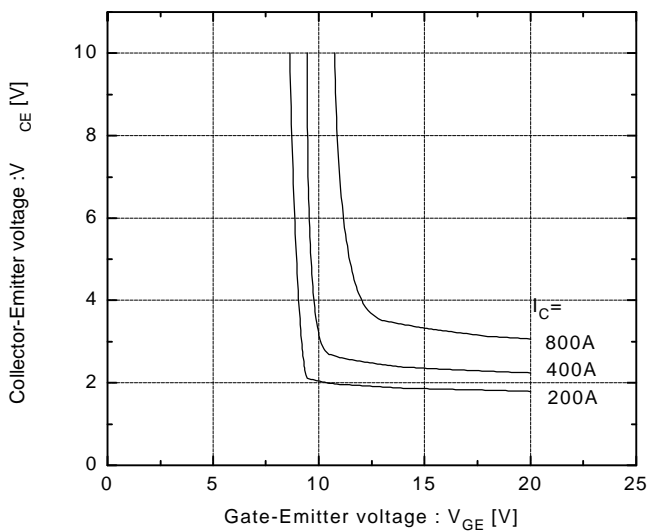
Collector current vs. Collector-Emmitter voltage

$T_j=125^\circ\text{C}$



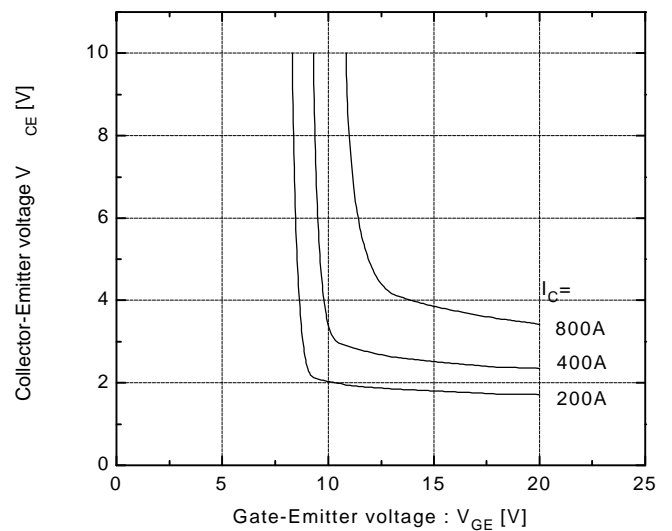
Collector-Emmitter vs. Gate-Emmitter voltage

$T_j=25^\circ\text{C}$

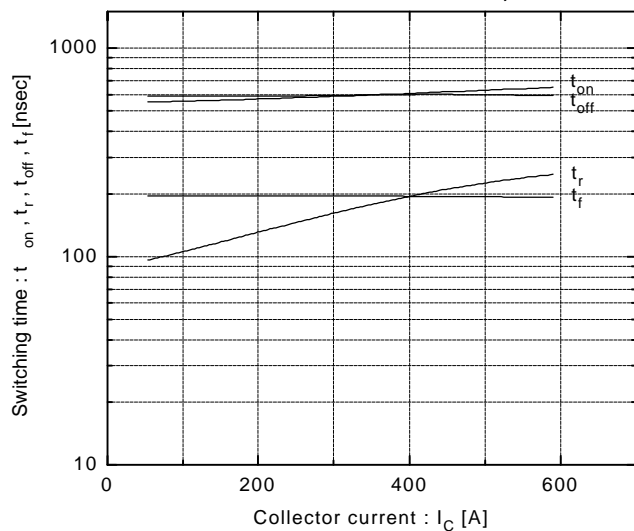


Collector-Emmitter vs. Gate-Emmitter voltage

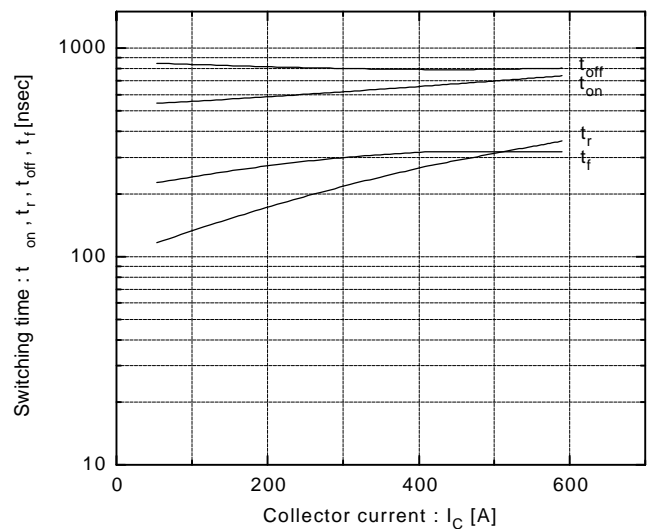
$T_j=125^\circ\text{C}$



Switching time vs. Collector current
 $V_{CC}=300\text{V}, R_G=4.7\Omega, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$

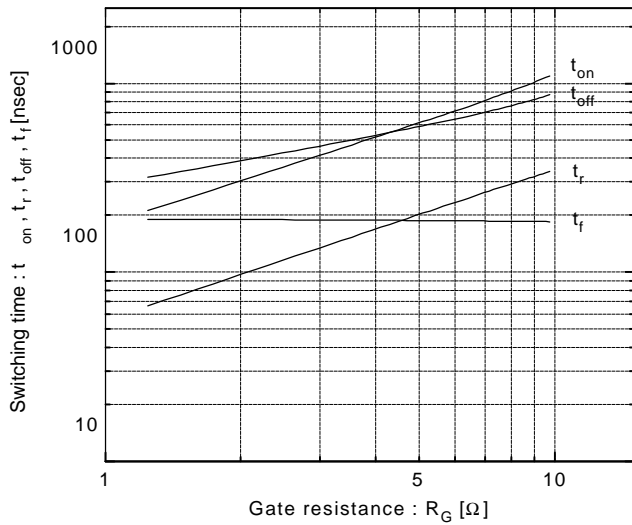


Switching time vs. Collector current
 $V_{CC}=300\text{V}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$



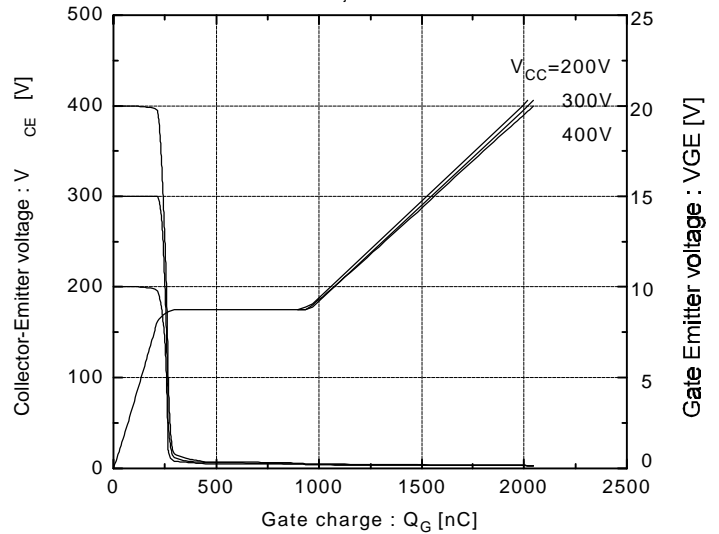
Switching time vs. R_G

$V_{CC}=300V, I_C=400A, V_{GE}=\pm 15V, T_j=25^\circ C$



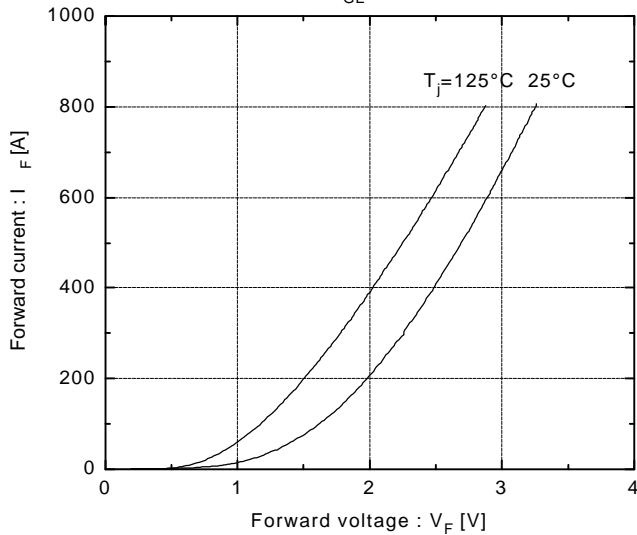
Dynamic input characteristics

$T_j=25^\circ C$



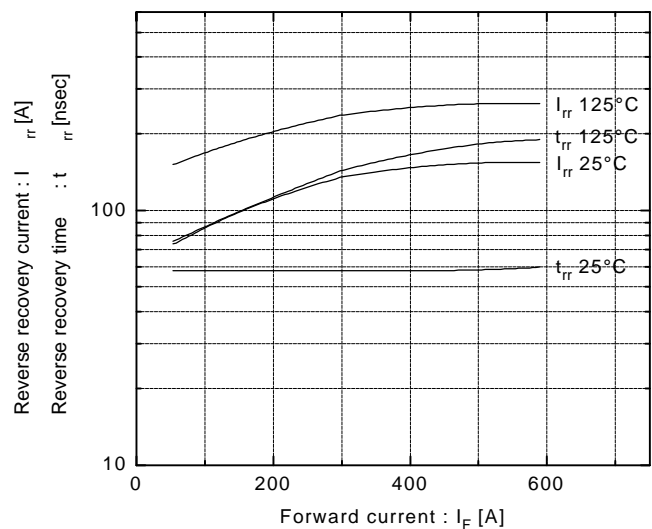
Forward current vs. Forward voltage

$V_{GE}=0V$

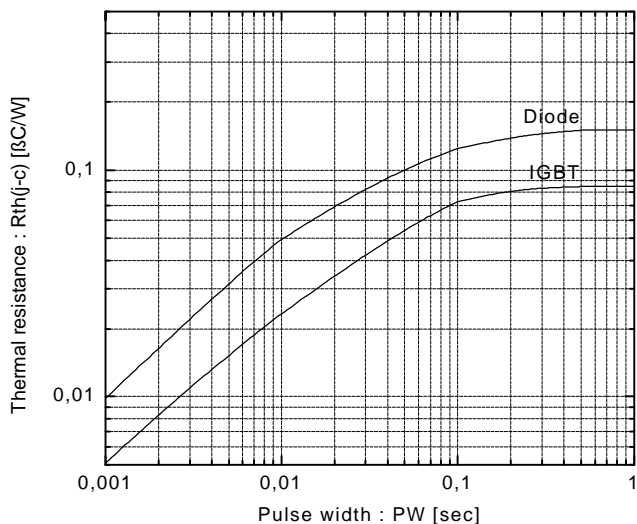


Reverse recovery characteristics

t_{rr}, I_{rr} vs. I_F

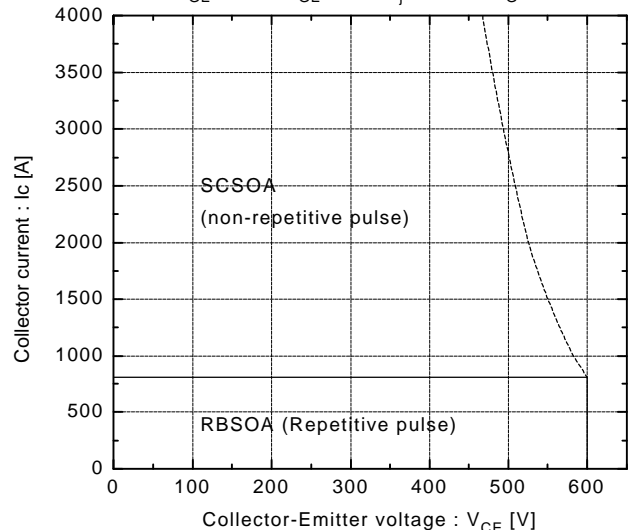


Transient thermal resistance



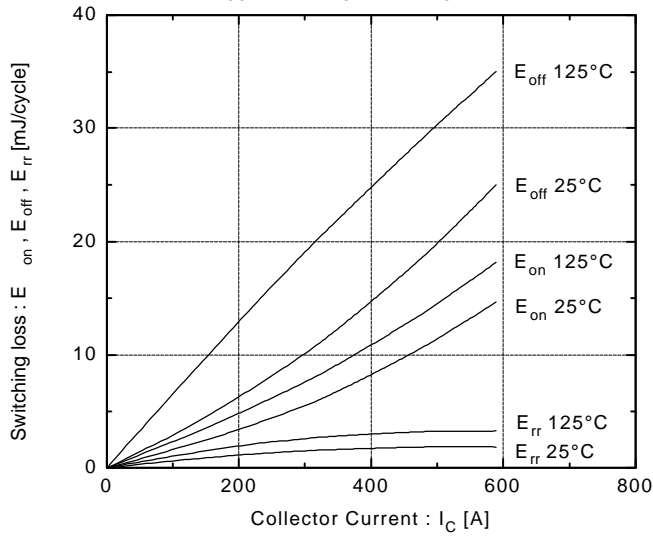
Reversed biased safe operating area

$+V_{GE}=15V, -V_{GE}\leq 15V, T_j\leq 125^\circ C, R_G\geq 4.7\Omega$



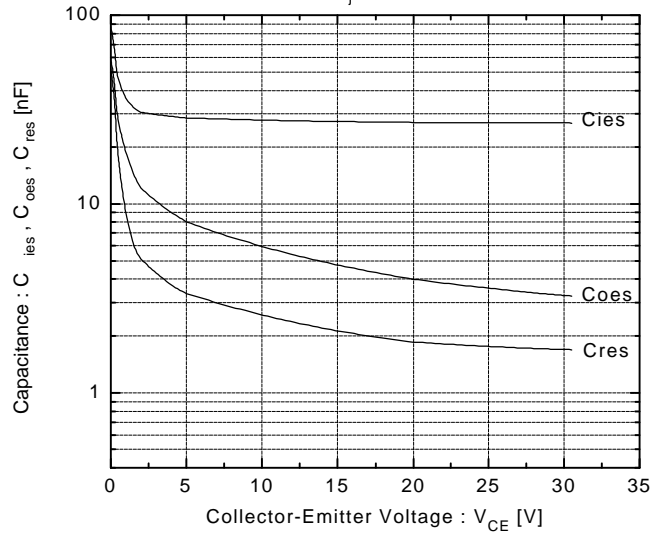
Switching loss vs. Collector current

$V_{CC}=300V, R_G=4.7\Omega, V_{GE}=\pm 15V$



Capacitance vs. Collector-Emitter voltage

$T_j=25^\circ C$



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